

In the Claims

Please amend the correspondingly numbered claims as follows:

Claims 1-18 (cancelled)

19. (previously amended) A method for removing reaction products of aluminum and a halogen from semiconductor process equipment, the method comprising forcing steam through holes in the semiconductor process equipment to remove the reaction products from the holes.
20. (cancelled)
21. (previously amended) The method of claim 19, wherein the halogen is fluorine.
22. (previously amended) The method of claim 19, wherein the steam is of a steam pressure above one atmosphere.
23. (previously amended) The method of claim 19, wherein the steam is of a steam temperature above 212 degrees Fahrenheit.
24. (original) The method of claim 19, wherein the equipment comprises a gas diffusion plate perforated with the holes.
25. (original) The method of claim 19, further comprising soaking the equipment prior to forcing the steam through the holes.
26. (original) The method of claim 25, wherein equipment is soaked in water.
27. (original) The method of claim 26, wherein the water is above 180 degrees Fahrenheit.

28. (previously amended) The method of claim 25, wherein the equipment is soaked at a pressure greater than one atmosphere.

Claims 29-33 (cancelled)

34. (amended) A method for removing reaction products of aluminum and a halogen from a component of semiconductor process equipment, the component having at least one component channel contaminated with the reaction product, the method comprising:

- a. providing a steam source ~~adapted to produce~~ that produces steam at a pressure greater than atmospheric pressure; and
- b. directing the steam through the channel, the steam removing the reaction products of aluminum and the halogen from the channel of the component of the semiconductor process equipment.

35. (previously added) The method of claim 34, wherein the halogen is fluorine.

36. (amended) The method of claim 34, wherein the steam is of a steam temperature of above at least 212 degrees Fahrenheit.

37. (previously added) The method of claim 34, wherein the equipment comprises a gas diffusion plate, and wherein the channel comprises a hole perforating the diffusion plate.

38. (previously added) The method of claim 34, further comprising soaking the component prior to directing the steam through the channel.

39. (previously added) The method of claim 38, wherein the component is soaked in water.

40. (previously added) The method of claim 39, wherein the water is above 180 degrees Fahrenheit.
41. (previously added) The method of claim 40, wherein the equipment is soaked at a pressure greater than one atmosphere.
42. (amended) The method of claim 34, further comprising directing a reducing agent ionized gas with the steam.
43. (amended) The method of claim 42, wherein the reducing agent ionized gas includes at least one of ionized hydrogen and ionized nitrogen.
44. (previously added) The method of claim 34, wherein the component comprises aluminum.
45. (previously added) The method of claim 34, wherein the reaction product comprises a layer formed during a semiconductor etch process.
46. (amended) The method of claim 45, wherein the semiconductor process equipment processes semiconductor devices having silicon and metal layer comprises silicon.